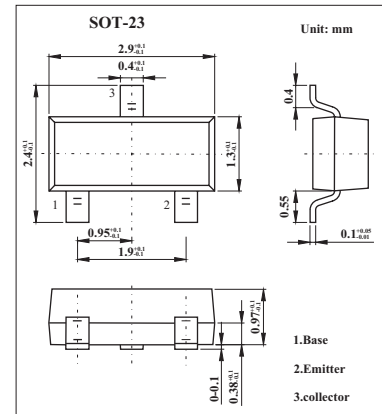


## NPN Epitaxial Planar Silicon Transistor

## 2SC3134

## ■ Features

- High  $V_{EBO}$ .
- Wide ASO and high durability against breakdown.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	15	V
Collector current	$I_C$	150	mA
Collector current (pulse)	$I_{CP}$	300	mA
Collector dissipation	$P_C$	200	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=10\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	90		560	
Gain bandwidth product	$f_T$	$V_{CE}=6\text{V}, I_C=1\text{mA}$		100		MHz
Output capacitance	$C_{ob}$	$V_{CB}=6\text{V}, f=1\text{MHz}$		2.2		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.5	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, R_{BE}=\infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	15			V

■  $h_{FE}$  Classification

Marking	H			
Rank	4	5	6	7
$h_{FE}$	90~180	135~270	200~400	300~600